

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|--|---|---------------------|
| 2 | 767 | (tft or thin adj film adj transistor) and etching near gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:34 |
| 3 | 271 | polysilicon and ((tft or thin adj film adj transistor) and etching near gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:34 |
| 4 | 53 | thinning and ((tft or thin adj film adj transistor) and etching near gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:39 |
| 5 | 12 | ("5164806" "5300804" "5600154" "5614728" "5789778" "5834352" "5874329" "6017781" "6066535" "6188058" "6198140" "6225644").PN. | USPAT | 2004/05/26 10:36 |
| 6 | 4159 | (thining or etching) near gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:40 |
| 7 | 767 | ((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:40 |
| 8 | 243 | cmos and (((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:40 |
| 9 | 162 | (ldd or lightly adj doped adj drain) and (cmos and (((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:56 |
| 10 | 1 | sacrificial adj gate and (cmos and (((tft or thin adj film adj transistor) and etching near gate) and ((thining or etching) near gate)-)-) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:56 |
| 11 | 16914 | (ldd or lightly adj doped adj drain) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:56 |
| 12 | 243 | sacrificial adj gate | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:56 |
| 13 | 72 | ((ldd or lightly adj doped adj drain)) and (sacrificial adj gate) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB | 2004/05/26 10:57 |